100mA / 50V Digital transistors (with built-in resistor)

DTC114GUA / DTC114GKA / DTC114GSA

Applications

Inverter, Interface, Driver

Features

- The built-in bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input, and parasitic effects are almost completely eliminated.
- 2) Only the on / off conditions need to be set for operation, making the device design easy.
- 3) Higher mounting densities can be achieved.

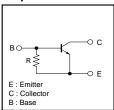
●Structure

NPN epitaxial planar silicon transistor (Resistor built-in type)

Packaging specifications

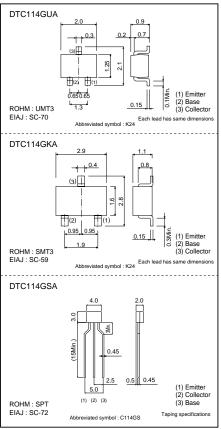
| | Package | UMT3 | SMT3 | SPT |
|-----------|------------------------------|--------|--------|--------|
| | Packaging type | Taping | Taping | Taping |
| | Code | T106 | T146 | TP |
| Part No. | Basic ordering unit (pieces) | 3000 | 3000 | 5000 |
| DTC114GUA | | 0 | - | - |
| DTC114GKA | | - | 0 | _ |
| DTC114GSA | | - | - | 0 |

●Equivalent circuit



R=10kΩ

●External dimensions (Unit : mm)



● Absolute maximum ratings (Ta=25°C)

| F | Parameter | Symbol | Limits | Unit | |
|-----------------------------|-----------------------|--------|-------------|------|--|
| Collector-base voltage | | Vсво | 50 | V | |
| Collector-emitter voltage | | VCEO | 50 | V | |
| Emitter-base voltage | | VEBO | 5 | V | |
| Collector current | | Ic | 100 | mA | |
| Collector Power dissipation | DTC114GUA / DTC114GKA | Pc | 200 | mW | |
| | DTC114GSA | PC | 300 | | |
| Junction temperature | | Tj | 150 | °C | |
| Storage temperature | | Tstg | -55 to +150 | °C | |

●Electrical characteristics (Ta=25°C)

| Parameter | Symbol | Min. | Тур. | Max. | Unit | Conditions |
|--------------------------------------|--------------|------|------|------|------|--------------------------------|
| Collector-base breakdown voltage | ВУсво | 50 | - | - | V | Ic=50μA |
| Collector-emitter breakdown voltage | BVceo | 50 | - | - | V | Ic=1mA |
| Emitter-base breakdown voltage | ВVево | 5 | - | - | V | Iε=720μA |
| Collector cutoff current | Ісво | - | - | 0.5 | μΑ | Vcb=50V |
| Emitter cutoff current | ІЕВО | 300 | - | 580 | μΑ | V _{EB} =4V |
| Collector-emitter saturation voltage | VCE(sat) | - | - | 0.3 | V | Ic=10mA, I _B =0.5mA |
| DC current transfer ratio | hfe | 30 | - | - | - | Ic=5mA, VcE=5V |
| Emitter-base resistance | R | 7 | 10 | 13 | kΩ | - |
| Transition frequency | f ⊤ * | - | 250 | - | MHz | Vce=10V, Ie= -5mA, f=100MHz |

^{*} Characteristics of built-in transistor

•Electrical characteristic curves

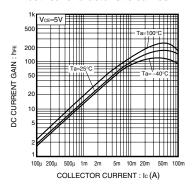


Fig.1 DC current gain vs. Collector current

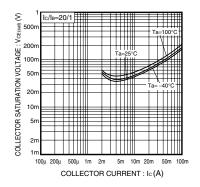


Fig.2 Collector-Emitter saturation voltage vs. Collector current

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Appendix1-Rev1.1